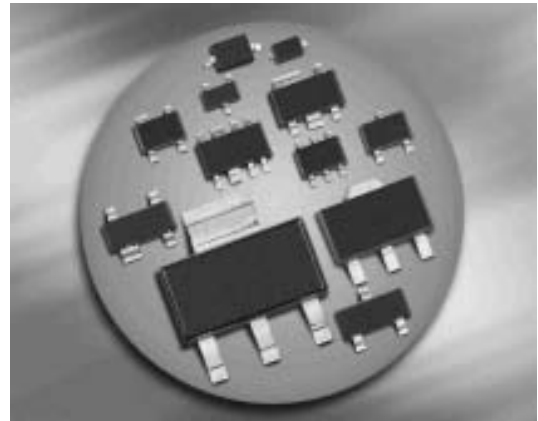
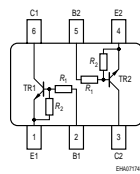
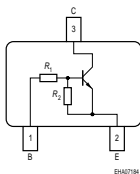


NPN Silicon Digital Transistor

- Switching circuit, inverter, interface circuit, driver circuit
- Built in bias resistor ($R_1=4.7\text{ k}\Omega$, $R_2=47\text{ k}\Omega$)
- BCR116S: Two internally isolated transistors with good matching in one multichip package
- BCR116S: For orientation in reel see package information below
- Pb-free (RoHS compliant) package ¹⁾
- Qualified according AEC Q101


BCR116/F
BCR116W
BCR116S


Type	Marking	Pin Configuration						Package
BCR116	WG _s	1=B	2=E	3=C	-	-	-	SOT23
BCR116F	WG _s	1=B	2=E	3=C	-	-	-	TSFP-3
BCR116S	WG _s	1=E1	2=B1	3=C2	4=E2	5=B2	6=C1	SOT363
BCR116W	WG _s	1=B	2=E	3=C	-	-	-	SOT323

¹Pb-containing package may be available upon special request

Maximum Ratings

Parameter	Symbol	Value	Unit
Collector-emitter voltage	V_{CEO}	50	V
Collector-base voltage	V_{CBO}	50	
Input forward voltage	$V_{i(fwd)}$	30	
Input reverse voltage	$V_{i(rev)}$	5	
Collector current	I_C	100	mA
Total power dissipation- BCR116, $T_S \leq 102^\circ\text{C}$ BCR116F, $T_S \leq 128^\circ\text{C}$ BCR116S, $T_S \leq 115^\circ\text{C}$ BCR116W, $T_S \leq 124^\circ\text{C}$	P_{tot}	200 250 250 250	mW
Junction temperature	T_j	150	°C
Storage temperature	T_{stg}	-65 ... 150	

Thermal Resistance

Parameter	Symbol	Value	Unit
Junction - soldering point ¹⁾	R_{thJS}		K/W
BCR116		≤ 240	
BCR116F		≤ 90	
BCR116S		≤ 140	
BCR116W		≤ 105	

¹⁾For calculation of R_{thJA} please refer to Application Note Thermal Resistance

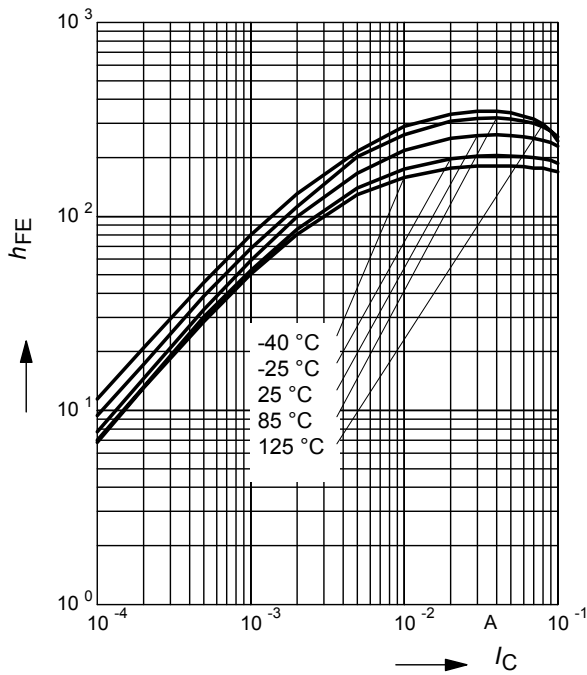
Electrical Characteristics at $T_A = 25^\circ\text{C}$, unless otherwise specified

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
DC Characteristics					
Collector-emitter breakdown voltage $I_C = 100 \mu\text{A}, I_B = 0$	$V_{(BR)CEO}$	50	-	-	V
Collector-base breakdown voltage $I_C = 10 \mu\text{A}, I_E = 0$	$V_{(BR)CBO}$	50	-	-	
Collector-base cutoff current $V_{CB} = 40 \text{V}, I_E = 0$	I_{CBO}	-	-	100	nA
Emitter-base cutoff current $V_{EB} = 5 \text{V}, I_C = 0$	I_{EBO}	-	-	155	μA
DC current gain ¹⁾ $I_C = 5 \text{mA}, V_{CE} = 5 \text{V}$	h_{FE}	70	-	-	-
Collector-emitter saturation voltage ¹⁾ $I_C = 10 \text{mA}, I_B = 0.5 \text{mA}$	V_{CEsat}	-	-	0.3	V
Input off voltage $I_C = 100 \mu\text{A}, V_{CE} = 5 \text{V}$	$V_{i(off)}$	0.4	-	0.8	
Input on voltage $I_C = 2 \text{mA}, V_{CE} = 0.3 \text{V}$	$V_{i(on)}$	0.5	-	1.4	
Input resistor	R_1	3.2	4.7	6.2	$\text{k}\Omega$
Resistor ratio	R_1/R_2	0.09	0.1	0.11	-
AC Characteristics					
Transition frequency $I_C = 10 \text{mA}, V_{CE} = 5 \text{V}, f = 100 \text{MHz}$	f_T	-	150	-	MHz
Collector-base capacitance $V_{CB} = 10 \text{V}, f = 1 \text{MHz}$	C_{cb}	-	3	-	pF

¹Pulse test: $t < 300\mu\text{s}$; $D < 2\%$

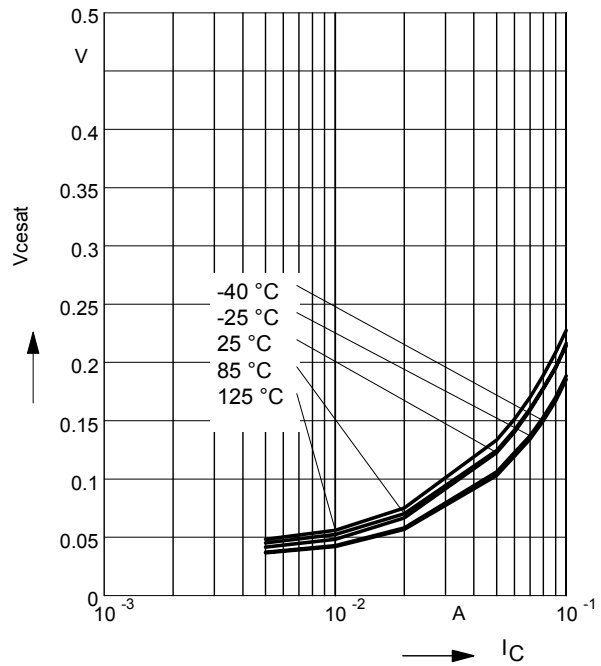
DC current gain $h_{FE} = f(I_C)$

$V_{CE} = 5V$ (common emitter configuration)



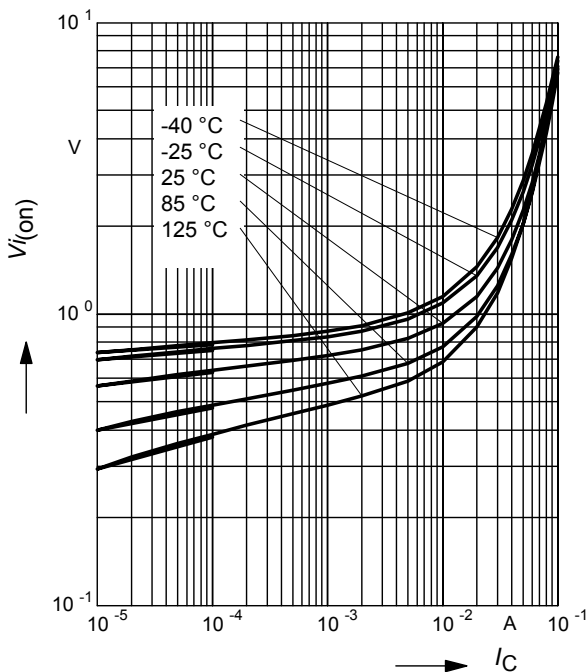
Collector-emitter saturation voltage

$V_{CEsat} = f(I_C), I_C/I_B = 20$



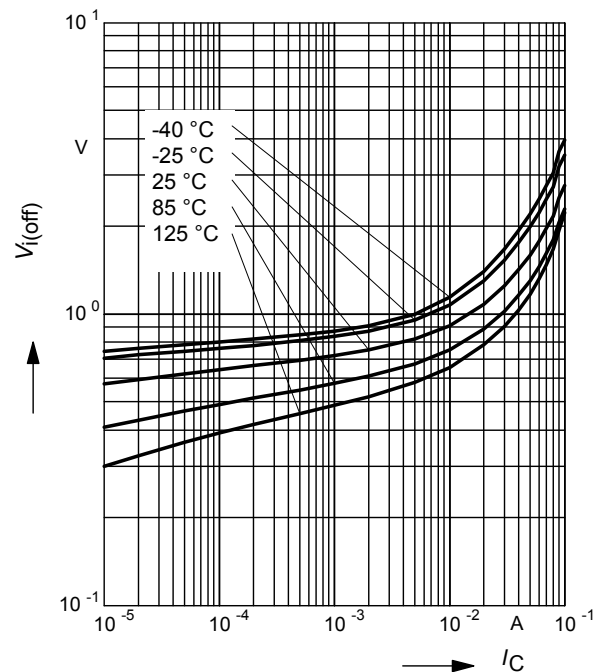
Input on Voltage $V_{i(on)} = f(I_C)$

$V_{CE} = 0.3V$ (common emitter configuration)



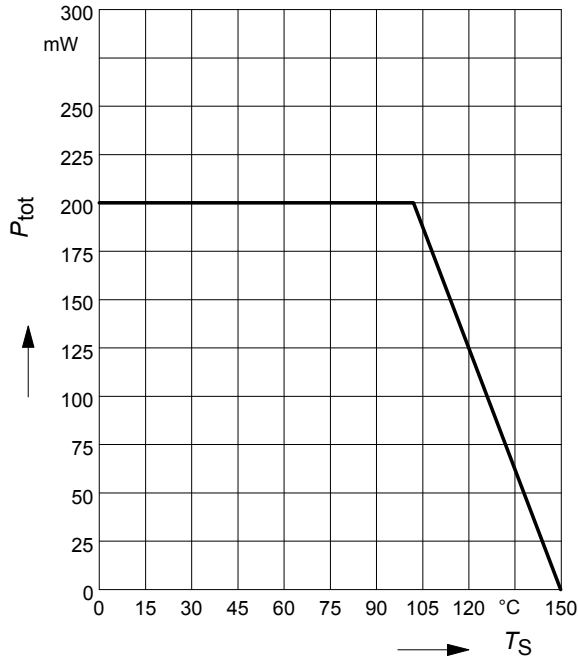
Input off voltage $V_{i(off)} = f(I_C)$

$V_{CE} = 5V$ (common emitter configuration)



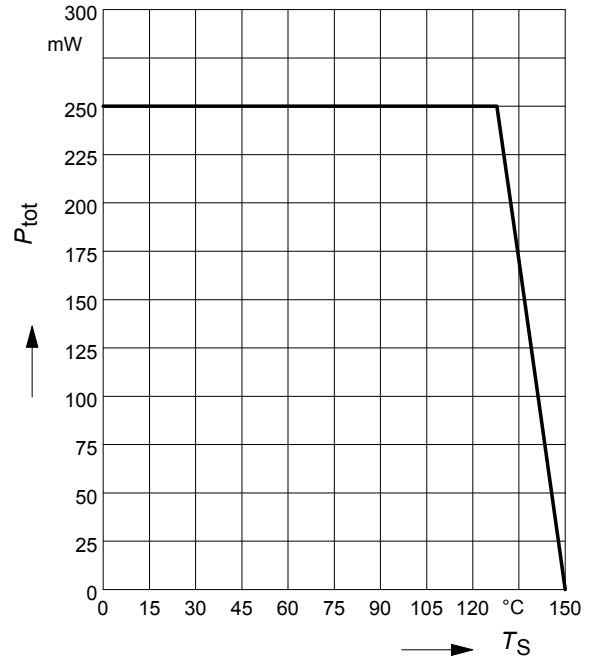
Total power dissipation $P_{tot} = f(T_S)$

BCR116



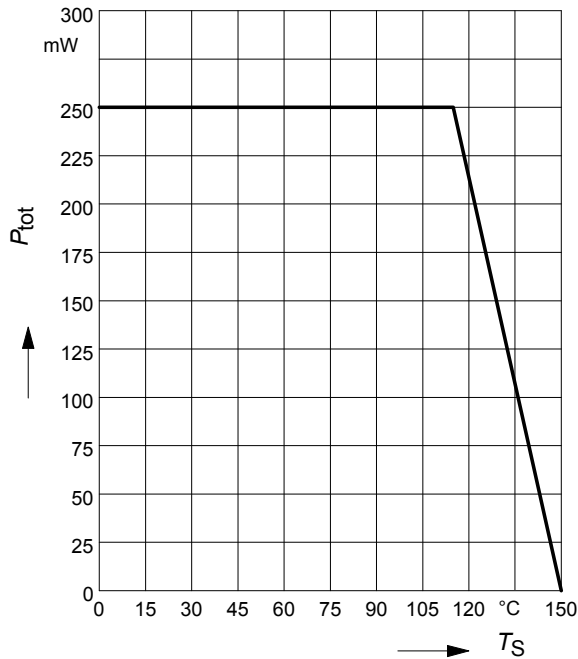
Total power dissipation $P_{tot} = f(T_S)$

BCR116F



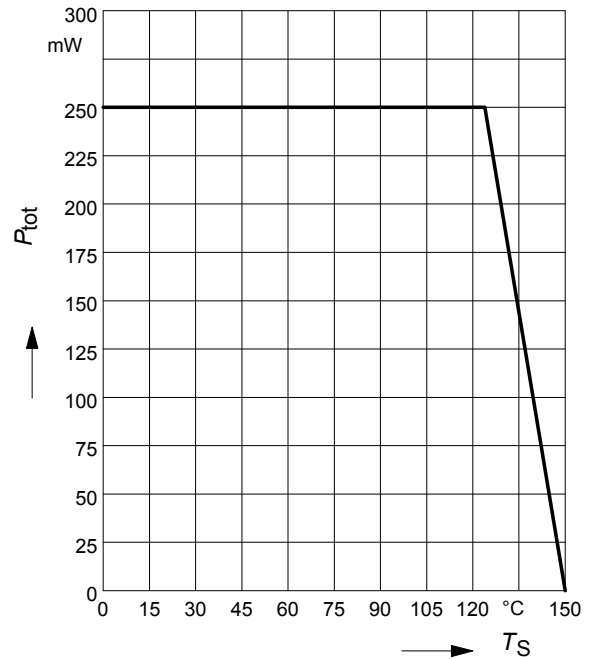
Total power dissipation $P_{tot} = f(T_S)$

BCR116S



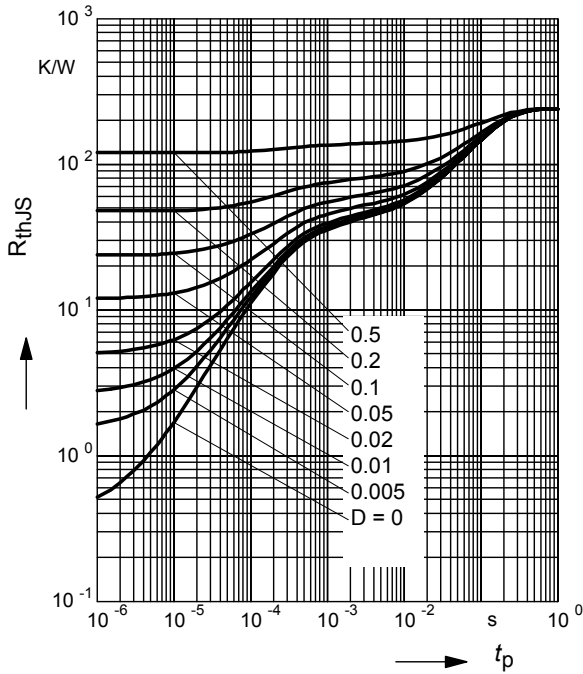
Total power dissipation $P_{tot} = f(T_S)$

BCR116W



Permissible Pulse Load $R_{thJS} = f(t_p)$

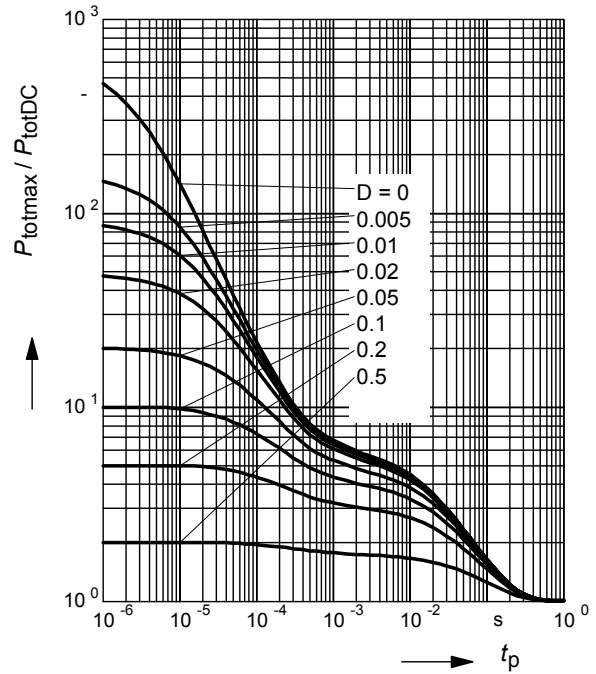
BCR116



Permissible Pulse Load

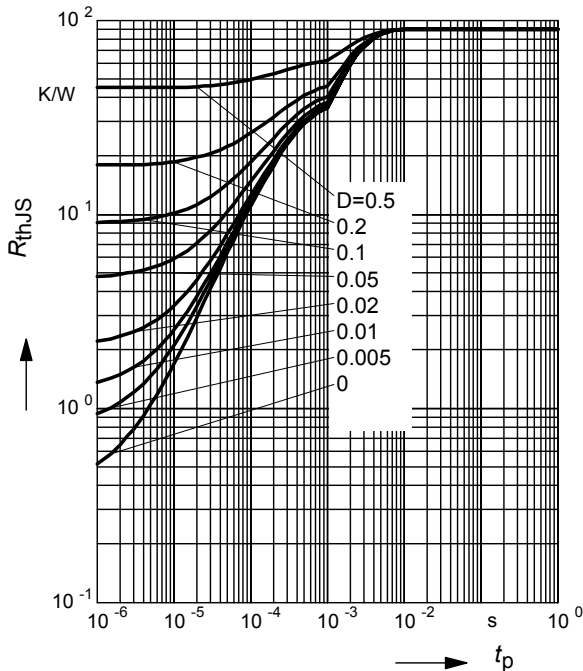
$P_{totmax}/P_{totDC} = f(t_p)$

BCR116



Permissible Puls Load $R_{thJS} = f(t_p)$

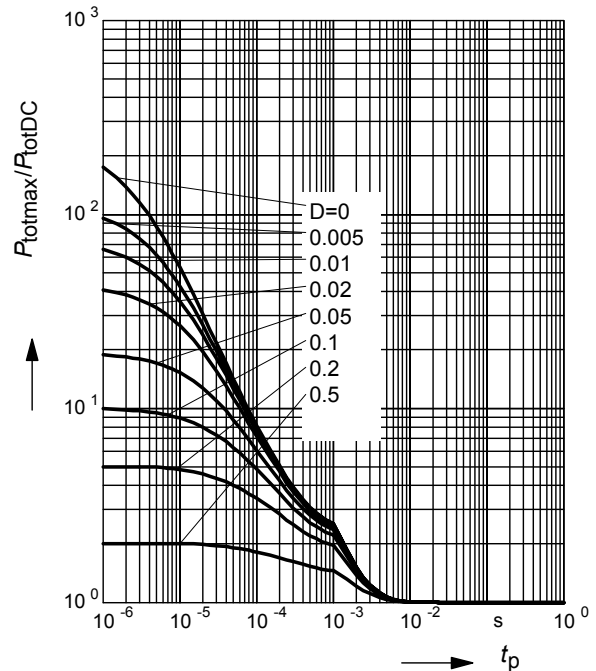
BCR116F



Permissible Pulse Load

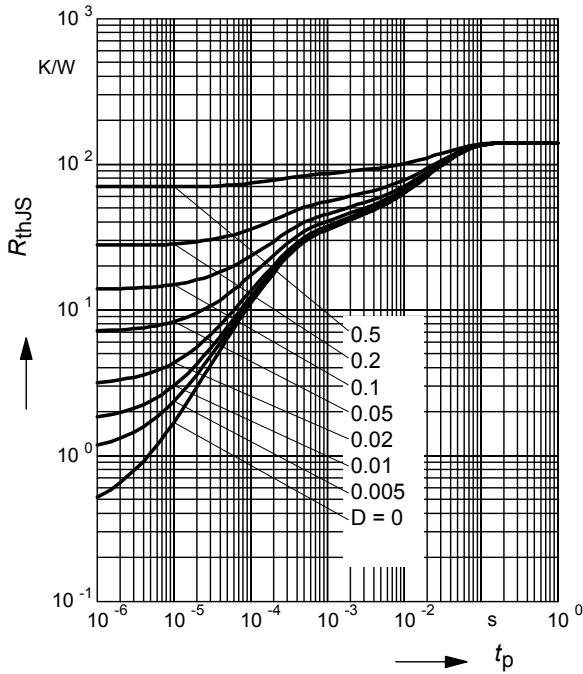
$P_{totmax}/P_{totDC} = f(t_p)$

BCR116F



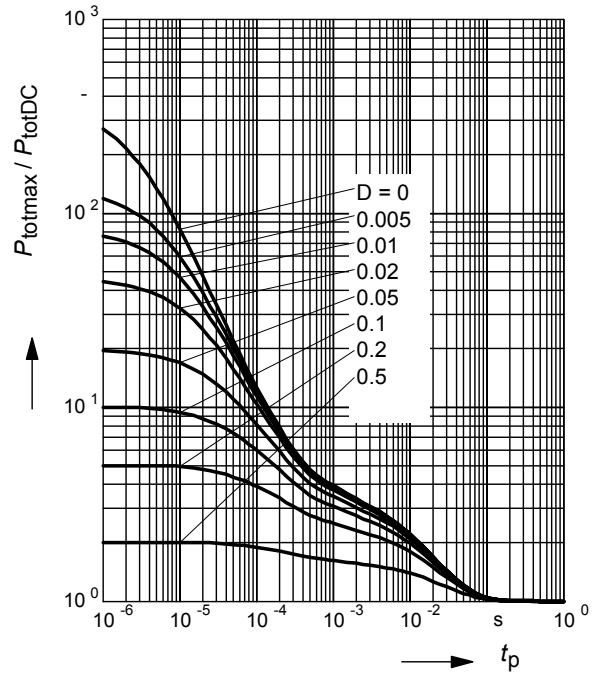
Permissible Puls Load $R_{thJS} = f(t_p)$

BCR116S



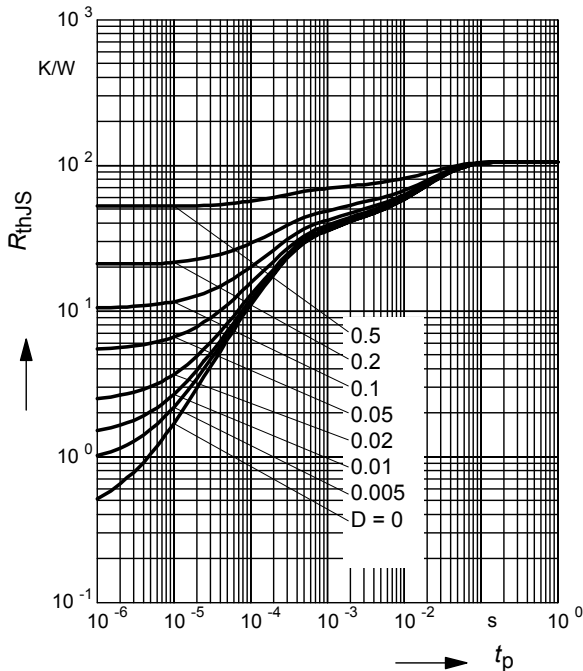
Permissible Pulse Load $P_{totmax}/P_{totDC} = f(t_p)$

BCR116S



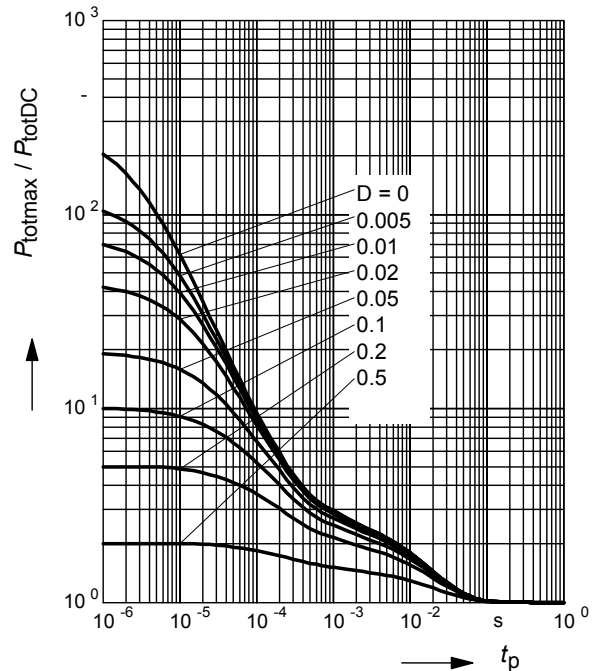
Permissible Puls Load $R_{thJS} = f(t_p)$

BCR116W

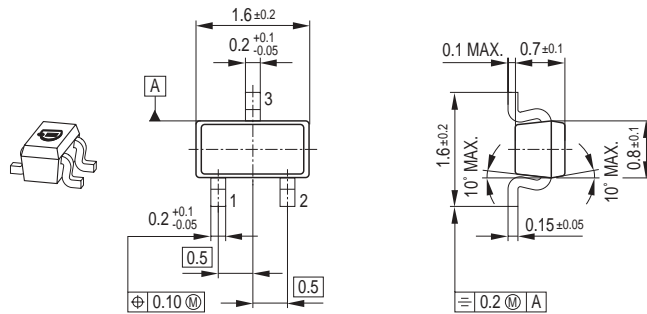


Permissible Pulse Load $P_{totmax}/P_{totDC} = f(t_p)$

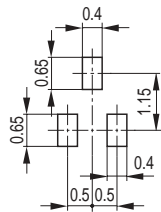
BCR116W



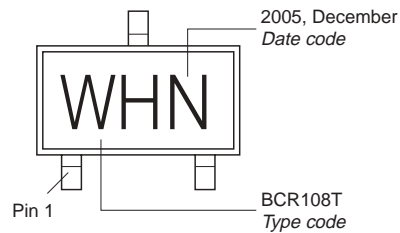
Package Outline



Foot Print

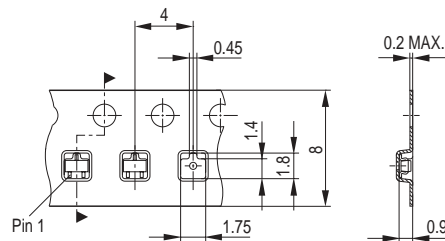


Marking Layout (Example)



Standard Packing

Reel $\varnothing 180 \text{ mm} = 3.000 \text{ Pieces/Reel}$
 Reel $\varnothing 330 \text{ mm} = 10.000 \text{ Pieces/Reel}$

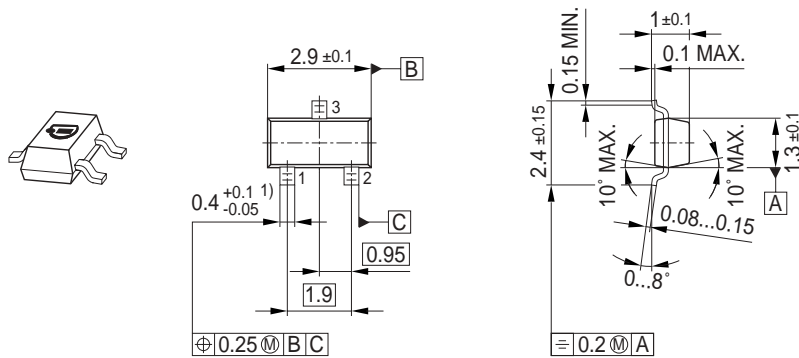


Date Code marking for discrete packages with one digit (SCD80, SC79, SC75¹⁾) CES-Code

Month	2003	2004	2005	2006	2007	2008	2009	2010	2011	2012	2013	2014
01	a	p	A	P	a	p	A	P	a	p	A	P
02	b	q	B	Q	b	q	B	Q	b	q	B	Q
03	c	r	C	R	c	r	C	R	c	r	C	R
04	d	s	D	S	d	s	D	S	d	s	D	S
05	e	t	E	T	e	t	E	T	e	t	E	T
06	f	u	F	U	f	u	F	U	f	u	F	U
07	g	v	G	V	g	v	G	V	g	v	G	V
08	h	x	H	X	h	x	H	X	h	x	H	X
09	j	y	J	Y	j	y	J	Y	j	y	J	Y
10	k	z	K	Z	k	z	K	Z	k	z	K	Z
11	l	2	L	4	l	2	L	4	l	2	L	4
12	n	3	N	5	n	3	N	5	n	3	N	5

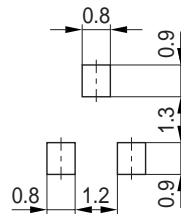
1) New Marking Layout for SC75, implemented at October 2005.

Package Outline

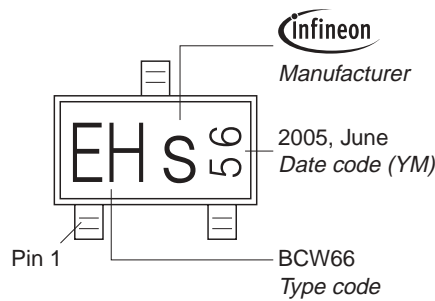


1) Lead width can be 0.6 max. in dambar area

Foot Print

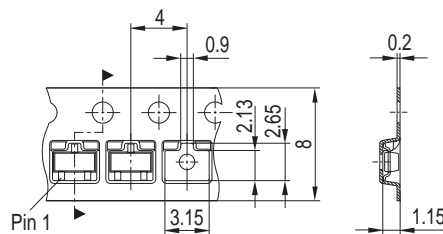


Marking Layout (Example)

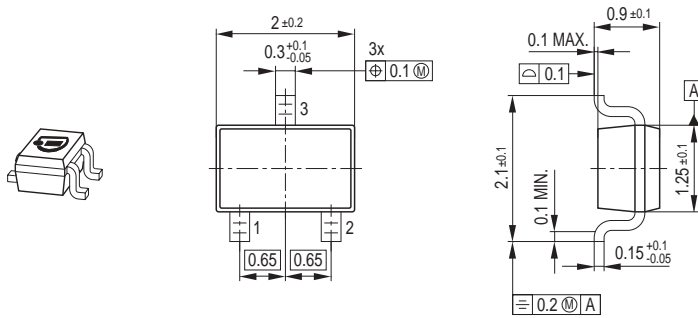


Standard Packing

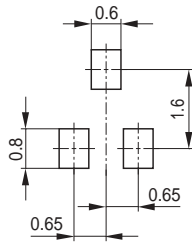
Reel ø180 mm = 3.000 Pieces/Reel
 Reel ø330 mm = 10.000 Pieces/Reel



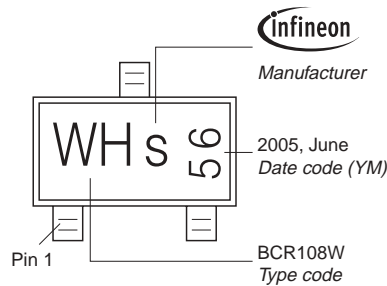
Package Outline



Foot Print

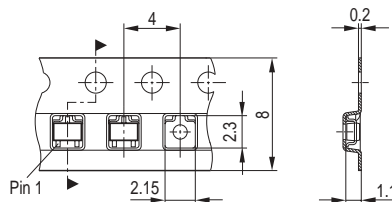


Marking Layout (Example)

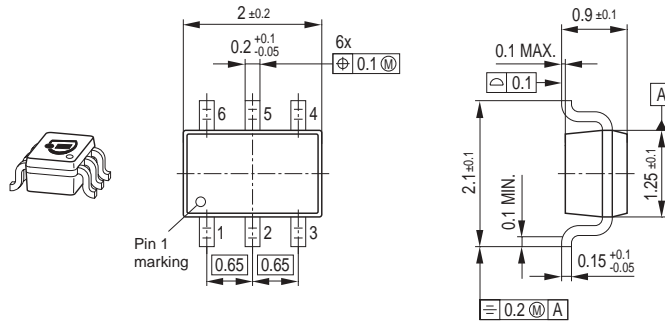


Standard Packing

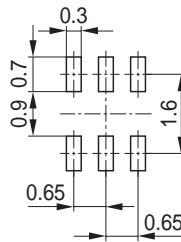
Reel $\varnothing 180 \text{ mm} = 3.000 \text{ Pieces/Reel}$
 Reel $\varnothing 330 \text{ mm} = 10.000 \text{ Pieces/Reel}$



Package Outline

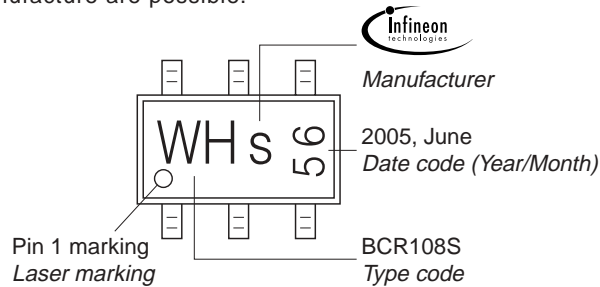


Foot Print



Marking Layout (Example)

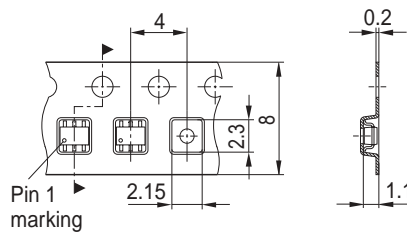
Small variations in positioning of Date code, Type code and Manufacture are possible.



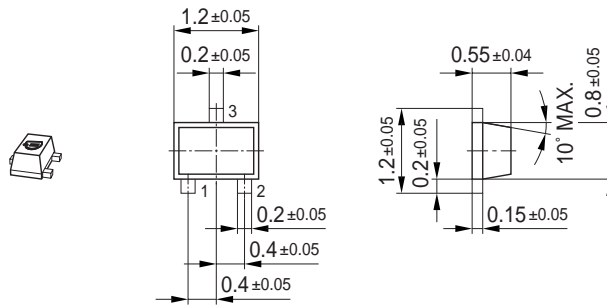
Standard Packing

Reel \varnothing 180 mm = 3.000 Pieces/Reel
 Reel \varnothing 330 mm = 10.000 Pieces/Reel

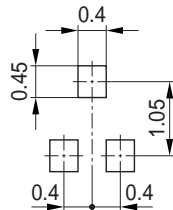
For symmetric types no defined Pin 1 orientation in reel.



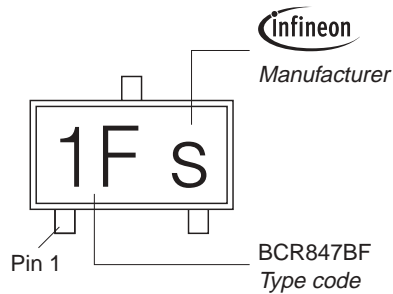
Package Outline



Foot Print

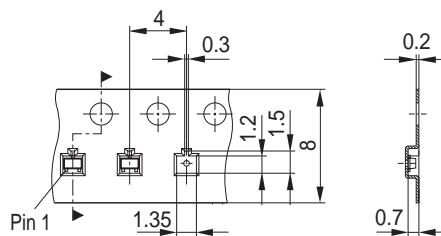


Marking Layout (Example)



Standard Packing

Reel \varnothing 180 mm = 3.000 Pieces/Reel
 Reel \varnothing 330 mm = 10.000 Pieces/Reel



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